# 2:1 MIPI D-PHY (1.5 Gbps) 4 Data Lane Switch

# **FSA634**

#### Description

The FSA634 is configured as a 4 data lane, MIPI D-PHY switch. This single pole double throw (SPDT) switch is optimized for switching between two high speed or low power MIPI sources. The FSA634 is designed for the MIPI specification and allows connection to a CSI or DSI module.

#### **Features**

Switch Type: SPDT (10x)Signal Type: MIPI, D-PHY

• V<sub>CC</sub>: 1.65 to 4.5 V

• Input Signal: 0 V to V<sub>CC</sub>

• R<sub>ON</sub>:

• 5 Ω Typical HS MIPI

5 Ω Typical LP MIPI
ΔR<sub>ON</sub>: 0.1 Ω Typical

• R<sub>ON\_FLAT</sub>: 0.06 Ω Typical

• I<sub>CCZ</sub>: 0.5 μA Maximum

• I<sub>CC</sub>: 32 μA Maximum

• O<sub>IRR</sub>: -30 dB Typical

• Bandwidth: 1.9 GHz Typical

• Xtalk: -38 dB Typical

• CON: 4.3 pF Typical

• Skew: 3 ps Typical

## **Applications**

• Cellular Phones, Smart Phones

• Tablets

• Laptops

• Displays



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(Bottom View)

WLCSP36, 2.06x2.06x0.432 CASE 567XU

#### **MARKING DIAGRAM**

VJKK XYZ

VJ = Specific Device Code

KK = Assembly Lot

X = Year

Y = Work Week

Z = Assembly Location

## **ORDERING INFORMATION**

See detailed ordering and shipping information on page 7 of this data sheet.

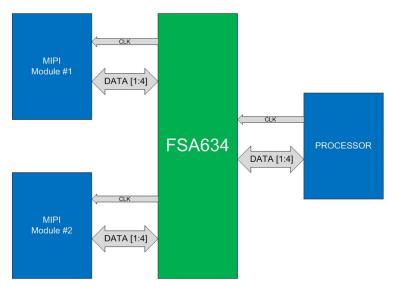
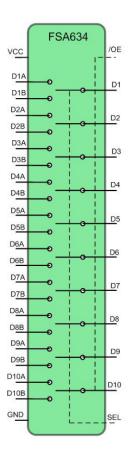


Figure 1. Typical Application

## **PIN DESCRIPTIONS**



PIN NAME	DESCRIPTION				
Dn	Common	Common Data Path			
DnA	Data Path	Data Path A			
DnB	Data Path B				
/OE	Output E	Output Enable			
051	Control	SEL=0	Dn = DnA		
SEL	Pin	Pin SEL=1 <u>Dn = DnB</u>			
VCC	Power				
GND	Ground				
NC	No Conne	ect			

Figure 2. Analog Symbol

# **PIN DEFINITIONS**

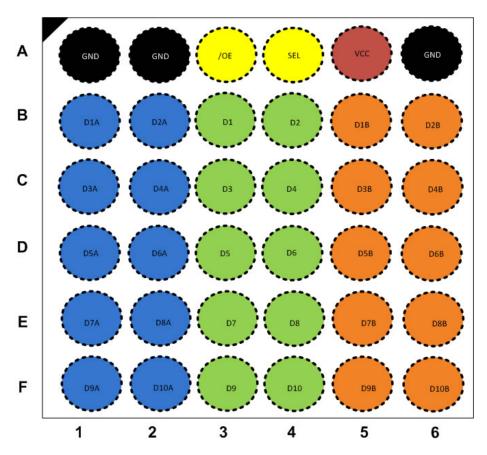


Figure 3. Top Through View

Table 1. BALL-TO-PIN MAPPINGS

Ball	Pin Name	Ball	Pin Name	Ball	Pin Name
A1	GND	C1	D3A	E1	D7A
A2	GND	C2	D4A	E2	D8A
А3	/OE	C3	D3	E3	D7
A4	SEL	C4	D4	E4	D8
A5	V <sub>CC</sub>	C5	D3B	E5	D7B
A6	GND	C6	D4B	E6	D8B
B1	D1A	D1	D5A	F1	D9A
B2	D2A	D2	D6A	F2	D10A
В3	D1	D3	D5	F3	D9
B4	D2	D4	D6	F4	D10
B5	D1B	D5	D5B	F5	D9B
В6	D2B	D6	D6B	F6	D10B

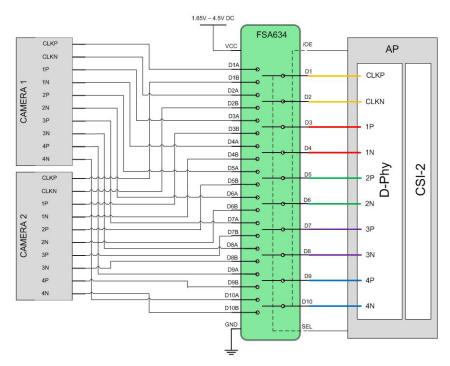


Figure 4. Suggested Configuration for 4 Lane D-PHY

## **TRUTH TABLE**

SEL	/OE	Function
LOW	LOW	Dn = DnA
HIGH	LOW	Dn = DnB
X	HIGH	All Ports High Impedance

## **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	Supply Voltage			5.25	V
V <sub>CNTRL</sub>	DC Input Voltage (/OE, SEL) (Note 1)			V <sub>CC</sub>	V
$V_{SW}$	DC Switch I/O Voltage (Note 1,2)			V <sub>CC</sub>	V
I <sub>IK</sub>	DC Input Diode Current				mA
I <sub>OUT</sub>	DC Output Current			50	mA
T <sub>STG</sub>	Storage Temperature			+150	°C
ESD	Human Body Model, JEDEC: JESD22-A114 All Pins				kV
	Charged Device Model, JEDEC: JESD22-C101				

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The input and output negative ratings may be exceeded if the input and output diode current ratings are observed.

2. V<sub>SW</sub> refers to analog data switch paths.

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	Supply Voltage	1.65	4.50	V	
V <sub>CNTRL</sub>	Control Input Voltage (SEL, /OE) (Note 3)		0	V <sub>CC</sub>	V
$V_{SW}$	Switch I/O Voltage (Dn, DAn, DBn)         HS Mode           LP Mode		0	0.425	V
			0	1.3	V
T <sub>A</sub>	Operating Temperature		-40	+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

3. The control inputs must be held HIGH or LOW; they must not float.

# **ELECTRICAL SPECIFICATION TABLE** Typical values are at $T_A = 25^{\circ}C$ , $V_{CC} = 3.3 \text{ V}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
ELECTRICAL PARA	METERS					
V <sub>IK</sub>	Clamp Diode Voltage	$I_{IN} = -18 \text{ mA}, V_{CC} = 1.8 \text{ V}$			-1.2	V
V <sub>IH</sub>	Input Voltage High	V <sub>CC</sub> = 1.65 V to 4.50 V	1.0			V
V <sub>IL</sub>	Input Voltage Low	V <sub>CC</sub> = 1.65 V to 4.50 V			0.4	V
I <sub>IN</sub>	Control Input Leakage (SEL,/OE)	$V_{SW} = 0 \text{ V to } V_{CC}, V_{CC} = 1.65 \text{ V to } 4.50 \text{ V}$	-500		500	nA
IN <sub>O(OFF)</sub> , IN <sub>C(OFF)</sub>	Off Leakage Current of Port Dn, DnA, DnB	Dn = 0.3 V to $V_{CC}$ – 0.3 V; DnA or DnB = Floating, 0.3 V, or $V_{CC}$ – 0.3 V; /OE = 0 V; $V_{CC}$ = 1.65 V to 4.5 V	-500		500	nA
I <sub>A(ON)</sub>	On Leakage Current of Common Ports (Dn)	$\begin{array}{l} \text{Dn} = 0.3 \text{ V to V}_{\text{CC}} - 0.3 \text{ V; DnA or DnB} = \\ \text{Floating, 0.3 V, or V}_{\text{CC}} - 0.3 \text{ V; /OE} = 0 \text{ V;} \\ \text{V}_{\text{CC}} = 1.65 \text{ V to 4.5 V} \end{array}$	-500		500	nA
I <sub>OFF</sub>	Power-Off Leakage Current	Dn, DnA or DnB; $V_{IN} = 0 \text{ V to } 4.5 \text{ V};$ $V_{CC} = 0 \text{ V}$	-500		500	nA
IOZ	Off-State Leakage	$0 \le Dn$ , $DnA$ , $DnB \le 3.6$ V, $/OE = High$ , $V_{CC} = 4.5$ V	-500		500	nA
R <sub>ON_MIPI_HS_1p8</sub>	Switch On Resistance for HS MIPI Applications	$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC} = 1.8$ V		5	12	Ω
R <sub>ON_MIPI_HS_2p5</sub>	(Note 5)	$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC} = 2.5$ V		5	9	Ω
R <sub>ON_MIPI_HS_3p6</sub>		$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC} = 3.6$ V		5	9	Ω
R <sub>ON_MIPI_HS_4p5</sub>		$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC} = 4.5$ V		5	9	Ω
R <sub>ON_MIPI_LP_1p8</sub>	Switch On Resistance for LP MIPI Applications	$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0 V, 0.6 V, 1.2 V, $V_{CC} = 1.8$ V		5	12	Ω
R <sub>ON_MIPI_LP_2p5</sub>	(Note 5)	$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0 V, 0.6 V, 1.2 V, $V_{CC} = 2.5$ V		5	9	Ω
R <sub>ON_MIPI_LP_3p6</sub>	7	$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0 V, 0.6 V, 1.2 V, $V_{CC} = 3.6$ V		5	9	Ω
R <sub>ON_MIPI_LP_4p5</sub>		I <sub>ON</sub> = -10 mA, /OE = 0 V, SEL = V <sub>CC</sub> or 0 V, DnA or DnB = 0 V, 0.6 V, 1.2 V V <sub>CC</sub> = 4.5 V		5	9	Ω

**ELECTRICAL SPECIFICATION TABLE** Typical values are at  $T_A = 25^{\circ}C$ ,  $V_{CC} = 3.3 \text{ V}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
OC ELECTRICAL PARAM	IETERS					
ΔR <sub>ON_MIPI_HS_1p8</sub>	On Resistance Matching Between HS MIPI Chan-	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 1.8 V		0.10		Ω
$\Delta R_{ON\_MIPI\_HS\_2p5}$	nels	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 2.5 V		0.10		Ω
ΔR <sub>ON_MIPI_HS_3p6</sub>	]	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 3.6 V		0.10		Ω
ΔR <sub>ON_MIPI_HS_4p5</sub>	]	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 4.5 V		0.10		Ω
ΔR <sub>ON_MIPI_LP_1p8</sub>	On Resistance Matching Between LP MIPI Chan-	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, $V_{CC}$ = 1.8 V		0.12		Ω
ΔR <sub>ON_MIPI_LP_2p5</sub>	nels	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, $V_{CC}$ = 2.5 V		0.12		Ω
ΔR <sub>ON_MIPI_LP_3p6</sub>		$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, $V_{CC}$ = 3.6 V		0.12		Ω
$\Delta R_{ON\_MIPI\_LP\_4p5}$		$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, $V_{CC}$ = 4.5 V		0.12		Ω
R <sub>ON_FLAT_MIPI_HS_1p8</sub>	On Resistance Flatness for HS MIPI Signals	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 1.8 V		0.04		Ω
R <sub>ON_FLAT_MIPI_HS_2p5</sub>		$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 2.5 V		0.06		Ω
R <sub>ON_FLAT_MIPI_HS_3p6</sub>	1	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 3.6 V		0.06		Ω
R <sub>ON_FLAT_MIPI_HS_4p5</sub>	1	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 4.5 V		0.06		Ω
R <sub>ON_FLAT_MIPI_LP_1p8</sub>	On Resistance Flatness for LP MIPI Signals	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, $V_{CC}$ = 1.8 V		0.18		Ω
R <sub>ON_FLAT_MIPI_LP_2p5</sub>	1	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, $V_{CC}$ = 2.5 V		0.28		Ω
R <sub>ON_FLAT_MIPI_LP_3p6</sub>		I <sub>ON</sub> = -10 mA, /OE = 0 V, SEL = V <sub>CC</sub> or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, V <sub>CC</sub> = 3.6 V		0.28		Ω
R <sub>ON_FLAT_MIPI_LP_4p5</sub>		I <sub>ON</sub> = -10 mA, /OE = 0 V, SEL = V <sub>CC</sub> or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, V <sub>CC</sub> = 4.5 V		0.28		Ω
I <sub>CCZ</sub>	Quiescent Hi–Z Supply Current	$V_{IN} = 0 \text{ V or } V_{CC}, I_{OUT} = 0 \text{ A, } V_{CC} = 4.5 \text{ V}$			0.5	μΑ
Icc	Quiescent Supply Current	$V_{IN} = 0$ or $V_{CC}$ , $I_{OUT} = 0$ A, $V_{CC} = 2.5$ V to 4.5 V		16	32	μΑ
I <sub>CC_1p8</sub>	1	$V_{IN} = 0$ or $V_{CC}$ , $I_{OUT} = 0$ A, $V_{CC} = 1.8$ V		15	25	μΑ
I <sub>CCT_4p5</sub>	Increase in I <sub>CC</sub> Current	V <sub>SEL</sub> = 1.65 V, /OE = 1.65 V, V <sub>CC</sub> = 4.5 V			4	μΑ
I <sub>CCT_2p5</sub>	Per Control Voltage and V <sub>CC</sub>	V <sub>SEL</sub> = 1.65 V, /OE = 1.65 V, V <sub>CC</sub> = 2.5 V			0.1	μΑ
C ELECTRICAL PARAM						
t <sub>INIT</sub>	Initalization Time V <sub>CC</sub> to Output	R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 5 pF, V <sub>SW</sub> = 1.2 V, V <sub>CC</sub> = 2.5 V to 4.5 V			100	μS
t <sub>INIT_1p8</sub>	7	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $V_{SW} = 1.2 V$ , $V_{CC} = 1.8 V$			150	μS
t <sub>EN</sub>	Enable Turn-On Time, /OE to Output	R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 5 pF, V <sub>SW</sub> = 1.2 V, V <sub>CC</sub> = 2.5 V to 4.5 V		120	200	ns
t <sub>EN_1p8</sub>	1	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $V_{SW} = 1.2 V$ , $V_{CC} = 1.8 V$		250	500	ns
t <sub>DIS</sub>	Disable Turn-Off Time, /OE to Output	$R_L$ = 50 $\Omega$ , $C_L$ = 5 pF, $V_{SW}$ = 1.2 V, $V_{CC}$ = 2.5 V to 4.5 V		25	50	ns
t <sub>DIS_1p8</sub>	1	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $V_{SW} = 1.2 V$ , $V_{CC} = 1.8 V$		50	90	ns

ELECTRICAL SPECIFICATION TABLE Typical values are at T<sub>A</sub> = 25°C, V<sub>CC</sub> = 3.3 V unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
LECTRICAL PAR	AMETERS			J.		<u></u>
t <sub>ON</sub>	Turn-On Time, SEL to Output	R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 5 pF, V <sub>SW</sub> = 1.2 V, V <sub>CC</sub> = 2.5 V to 4.5 V, SEL = H to L, SEL = L to H			200	ns
t <sub>ON_1p8</sub>		$R_L$ = 50 $\Omega$ , $C_L$ = 5 pF, $V_{SW}$ = 1.2 V, $V_{CC}$ = 1.8 V, SEL = H to L, SEL = L to H			300	ns
t <sub>OFF</sub>	Turn-Off Time SEL to Output	R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 5 pF, V <sub>SW</sub> = 1.2 V, V <sub>CC</sub> = 2.5 V to 4.5 V, SEL = H to L, SEL = L to H			200	ns
t <sub>OFF_1p8</sub>		$R_L$ = 50 $\Omega$ , $C_L$ = 5 pF, $V_{SW}$ = 1.2 V, $V_{CC}$ = 1.8 V, SEL = H to L, SEL = L to H			300	
t <sub>BBM</sub>	Break-Before-Make Time	$R_L$ = 50 $\Omega$ , $C_L$ = 5 pF, $V_{SW}$ = 1.2 V, $V_{CC}$ = 1.65 V to 4.5 V	10	50		ns
OIRR	Off Isolation for MIPI (Note 5)	$R_L = 50 \ \Omega, f = 750 \ MHz, /OE = V_{CC}, V_{SW} = -1 \ dBm \ (200 \ mV_{PP}), V_{CC} = 1.65 \ V \ to \ 4.5 \ V$		-30		dB
XTALK	Crosstalk for MIPI (Note 5)	$R_L = 50 \ \Omega, f = 750 \ MHz, V_{SW} = -1 \ dBm$ (200 mV <sub>PP</sub> ), $V_{CC} = 1.65 \ V$ to 4.5 V		-38		dB
BW	Bandwidth at -3dB (Note 5)	$R_L = 50 \Omega$ , $C_L = 0 pF$ , $V_{CC} = 3 V$		1.9		GHz
t <sub>SK(O)</sub>	Channel-to-Channel Sin- gle-Ended Skew (Note 5)	TDR-Based Method ( $V_{SW}$ = 0.2 $V_{PP}$ , $C_L$ = $C_{ON}$ ), $V_{CC}$ = 3.3 $V$		3	20	ps
<sup>t</sup> SK(P)	Skew of Opposite Transitions of the Same Output (Note 5)	TDR-Based Method ( $V_{SW}$ = 0.2 $V_{PP}$ , $C_L$ = $C_{ON}$ ), $V_{CC}$ = 3.3 $V$		3	20	ps
PACITANCE						
C <sub>IN</sub>	Control Pin Input Capacitance (Note 5)	V <sub>CC</sub> = 0 V, f = 1 MHz		2.7		pF
C <sub>ON</sub>	Out On Capacitance (Note 5)	V <sub>CC</sub> = 3.3 V, /OE = 0 V, f = 1 MHz		4.3		pF
C <sub>OFF</sub>	Out Off Capacitance (Note 5)	$V_{CC}$ and $/OE = 3.3 \text{ V, f} = 1 \text{ MHz}$		1.9		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTE: Guarantee Levels:

- 4. Guaranteed by Design. Characterized on the ATE or Bench.
- 5. Guaranteed by Design and Characterization, not Production Tested.

The table below pertains to the Packaging information on the following page.

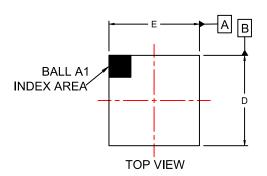
#### ORDERING INFORMATION

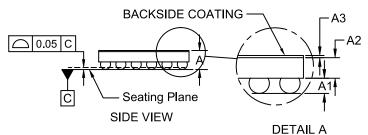
Part Number	Operating Temperature Range	Package	Top Mark
FSA634UCX	−40 to +85°C	36-Ball WLCSP, Non-JEDEC 2.06 x 2.06 mm, 0.35 mm Pitch	VJ

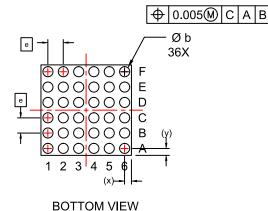
#### PACKAGE DIMENSIONS

#### WLCSP36 2.06x2.06x0.432

CASE 567XU **ISSUE O** 



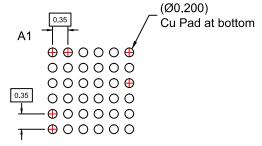




#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DATUM C APPLIES TO THE SPHERICAL CROWN OF THE SOLDER BALLS

	MILLIMETERS					
DIM	MIN.	NOM.	MAX.			
Α	0.391	0.432	0.473			
A1	0.154	0.174	0.194			
A2	0.215	0.233	0.251			
A3	0.022	0.025	0.028			
b	0.211	0.231	0.251			
D	2.03	2.06	2.09			
Е	2.03	2.06	2.09			
е	0.35 BSC					
х	0.140	0.155	0.170			
у	0.140	0.155	0.170			



## RECOMMENDED MOUNTING FOOTPRINT\* (NSMD PAD TYPE)

\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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